

ABSTRACT OF THE DISCLOSURE

The present invention discloses a method for aligning a key in a semiconductor device, which prevents misalignment in subsequent photo processes during a semiconductor key formation process. The method comprises the steps of: preparing a semiconductor substrate that is divided into a scribe lane region and a main chip region; depositing an oxide film on the semiconductor substrate for forming an align key; forming an area key and a first align key at the same time on the scribe lane region by selectively etching the oxide film by using a N-well ion implantation mask; performing a N-well ion implantation on the region which the oxide film is removed from; and forming a second align key in the area key, whose formation is already finished by removing the oxide film, by a silicon etching method using a P-well mask, upon a N-well process using a P-well ion implantation mask.